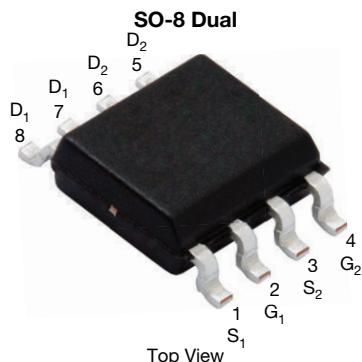
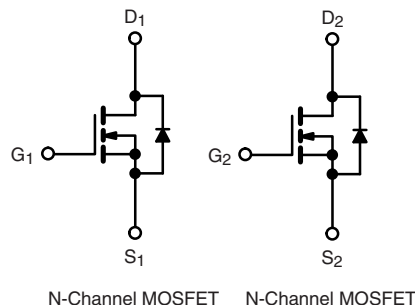


Automotive Dual N-Channel 60 V (D-S) 175 °C MOSFET



FEATURES

- TrenchFET® power MOSFET
- 100 % R_g and UIS tested
- AEC-Q101 qualified
- Material categorization: for definitions of compliance please see www.vishay.com/doc?99912



PRODUCT SUMMARY	
V_{DS} (V)	60
$R_{DS(on)}$ (Ω) at $V_{GS} = 10$ V	0.040
$R_{DS(on)}$ (Ω) at $V_{GS} = 4.5$ V	0.055
I_D (A) per leg	7
Configuration	Dual

ORDERING INFORMATION	
Package	SO-8
Lead (Pb)-free and Halogen-free	SQ4946CEY (for detailed order number please see www.vishay.com/doc?79776)

ABSOLUTE MAXIMUM RATINGS ($T_C = 25$ °C, unless otherwise noted)				
PARAMETER		SYMBOL	LIMIT	UNIT
Drain-source voltage		V_{DS}	60	V
Gate-source voltage		V_{GS}	± 20	
Continuous drain current	$T_C = 25$ °C	I_D	7	A
	$T_C = 125$ °C		4	
Continuous source current (diode conduction) ^a		I_S	3.6	
Pulsed drain current ^b		I_{DM}	28	
Single pulse avalanche current		I_{AS}	18	
Single pulse avalanche energy		E_{AS}	16.2	mJ
Maximum power dissipation	$T_C = 25$ °C	P_D	4	W
	$T_C = 125$ °C		1.3	
Operating junction and storage temperature range		T_J, T_{stg}	-55 to +175	°C

THERMAL RESISTANCE RATINGS				
PARAMETER		SYMBOL	LIMIT	UNIT
Junction-to-ambient	PCB mount ^c	R_{thJA}	110	°C/W
Junction-to-foot (drain)		R_{thJF}	34	

Notes

- Package limited
- Pulse test; pulse width ≤ 300 μ s, duty cycle ≤ 2 %
- When mounted on 1" square PCB (FR4 material)



SPECIFICATIONS (T _C = 25 °C, unless otherwise noted)							
PARAMETER	SYMBOL	TEST CONDITIONS		MIN.	TYP.	MAX.	UNIT
Static							
Drain-source breakdown voltage	V _{DS}	V _{GS} = 0 V, I _D = 250 μA		60	-	-	V
Gate-source threshold voltage	V _{GS(th)}	V _{DS} = V _{GS} , I _D = 250 μA		1.5	2.0	2.5	
Gate-source leakage	I _{GSS}	V _{DS} = 0 V, V _{GS} = ± 20 V		-	-	± 100	nA
Zero gate voltage drain current	I _{DSS}	V _{GS} = 0 V	V _{DS} = 60 V	-	-	1	μA
		V _{GS} = 0 V	V _{DS} = 60 V, T _J = 125 °C	-	-	50	
		V _{GS} = 0 V	V _{DS} = 60 V, T _J = 175 °C	-	-	150	
On-state drain current ^a	I _{D(on)}	V _{GS} = 10 V	V _{DS} ≥ 5 V	20	-	-	A
Drain-source on-state resistance ^a	R _{DS(on)}	V _{GS} = 10 V	I _D = 4.5 A	-	0.033	0.040	Ω
		V _{GS} = 10 V	I _D = 4.5 A, T _J = 125 °C	-	-	0.066	
		V _{GS} = 10 V	I _D = 4.5 A, T _J = 175 °C	-	-	0.081	
		V _{GS} = 4.5 V	I _D = 4 A	-	0.045	0.055	
Forward transconductance ^b	g _{fs}	V _{DS} = 15 V, I _D = 4.5 A		-	15	-	S
Dynamic ^b							
Input capacitance	C _{iss}	V _{GS} = 0 V	V _{DS} = 25 V, f = 1 MHz	-	600	750	pF
Output capacitance	C _{oss}			-	110	140	
Reverse transfer capacitance	C _{rss}			-	50	62	
Total gate charge ^c	Q _g	V _{GS} = 10 V	V _{DS} = 30 V, I _D = 5.3 A	-	11.7	18	nC
Gate-source charge ^c	Q _{gs}			-	1.8	2.7	
Gate-drain charge ^c	Q _{gd}			-	2.8	4.2	
Gate resistance	R _g	f = 1 MHz		1.3	-	6	Ω
Turn-on delay time ^c	t _{d(on)}	V _{DD} = 30 V, R _L = 6.8 Ω I _D ≅ 4.4 A, V _{GEN} = 10 V, R _g = 1 Ω		-	7	11	ns
Rise time ^c	t _r			-	3.3	5	
Turn-off delay time ^c	t _{d(off)}			-	22.4	33.5	
Fall time ^c	t _f			-	2.1	3.2	
Source-Drain Diode Ratings and Characteristics ^b							
Pulsed current ^a	I _{SM}			-	-	28	A
Forward voltage	V _{SD}	I _F = 2 A, V _{GS} = 0 V		-	0.75	1.1	V
Body diode reverse recovery time	t _{rr}	I _F = 4.4 A, di/dt = 100 A/μs		-	20	40	ns
Body diode reverse recovery charge	Q _{rr}			-	17	34	nC
Reverse recovery fall time	t _a			-	15	-	ns
Reverse recovery rise time	t _b			-	5	-	
Body diode peak reverse recovery current	I _{RM(REC)}			-	-1.91	-	A

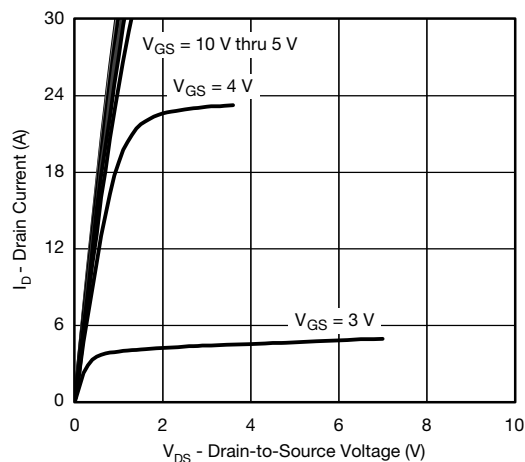
Notes

- a. Pulse test; pulse width $\leq 300\text{ }\mu\text{s}$, duty cycle $\leq 2\%$
b. Guaranteed by design, not subject to production testing
c. Independent of operating temperature

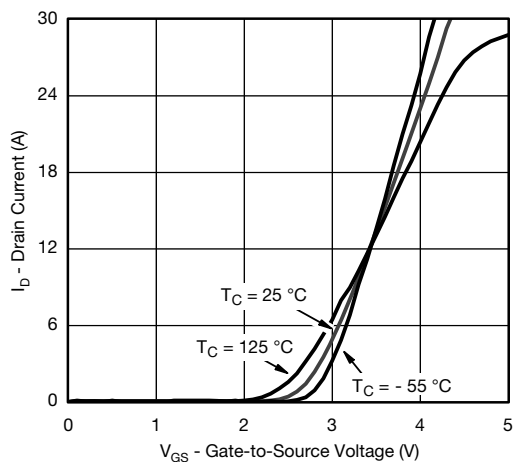
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.



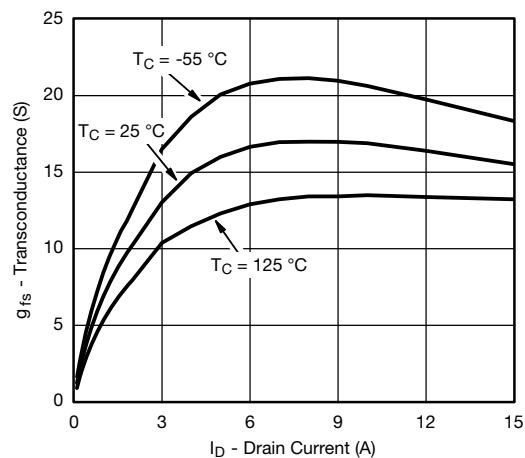
TYPICAL CHARACTERISTICS ($T_A = 25\text{ }^{\circ}\text{C}$, unless otherwise noted)



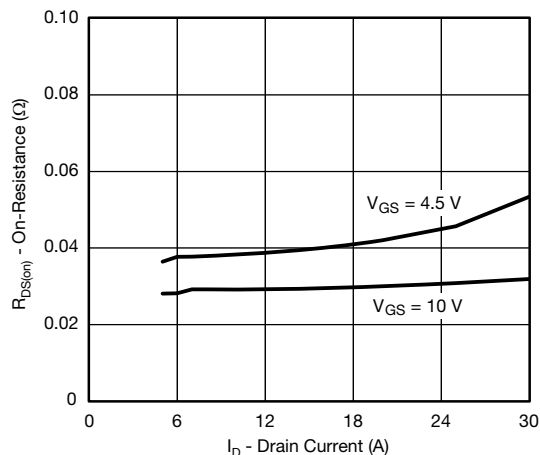
Output Characteristics



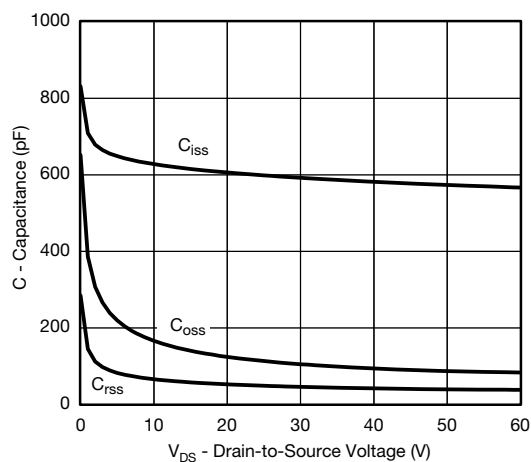
Transfer Characteristics



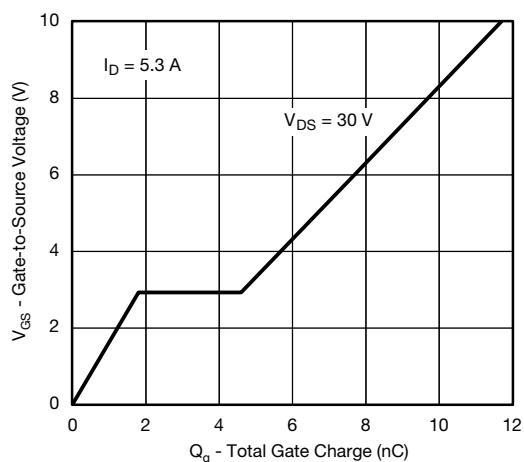
Transconductance



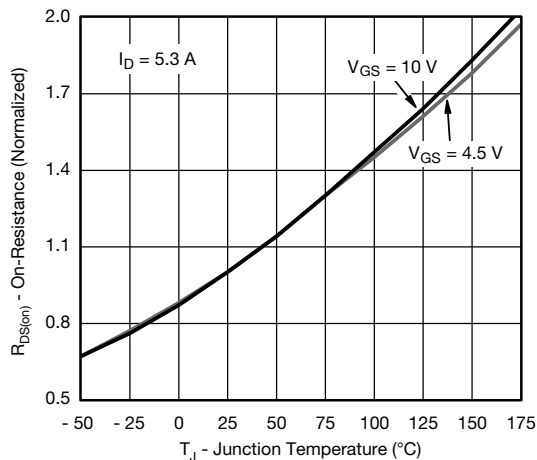
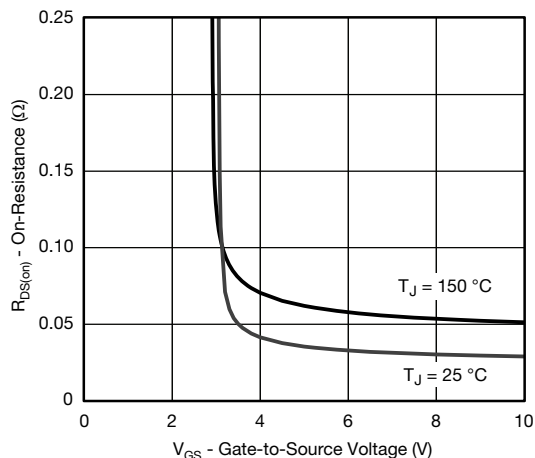
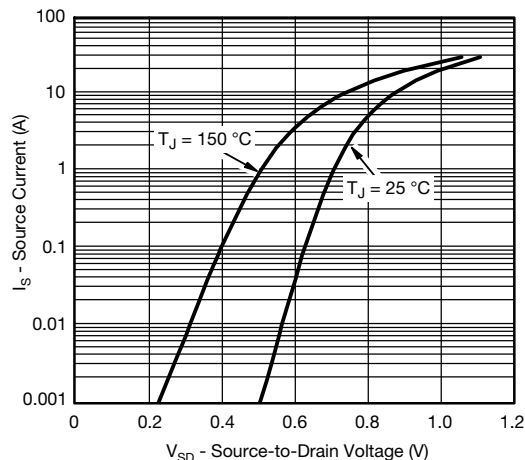
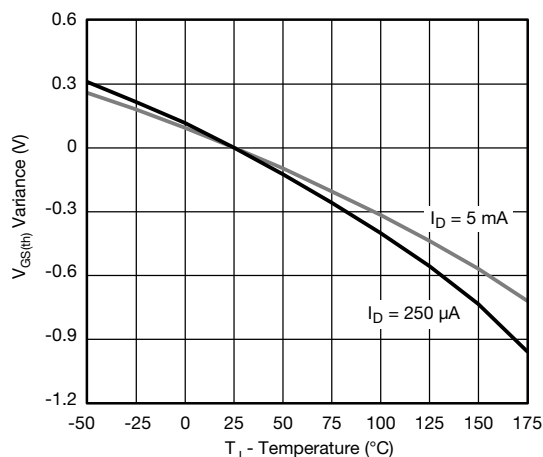
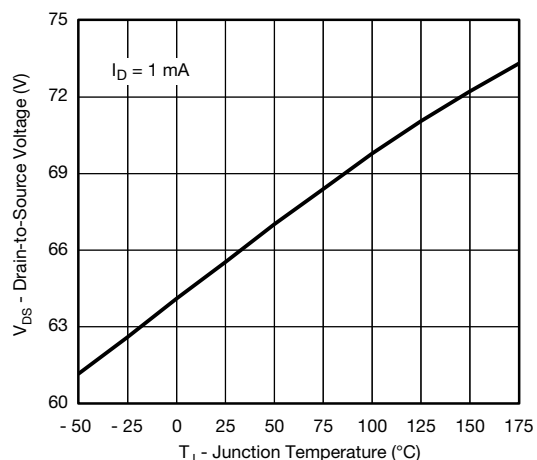
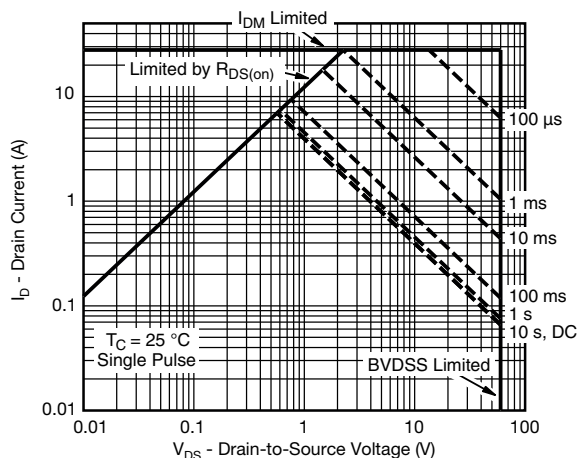
On-Resistance vs. Drain Current



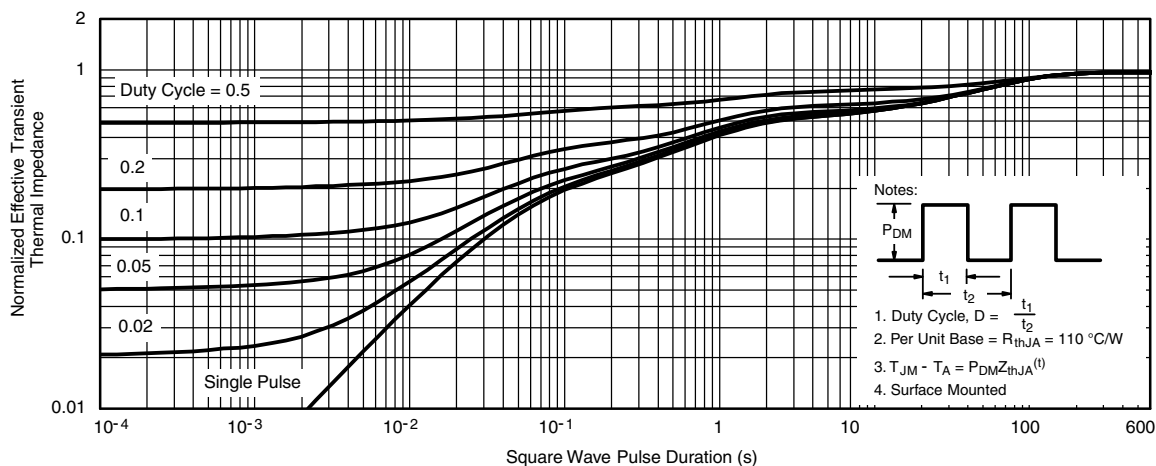
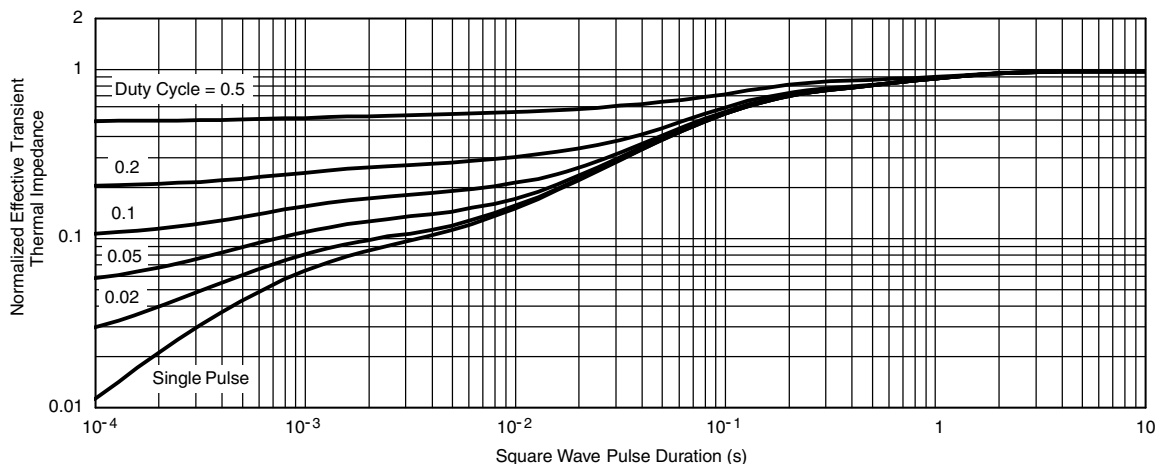
Capacitance



Gate Charge

TYPICAL CHARACTERISTICS ($T_A = 25\text{ }^{\circ}\text{C}$, unless otherwise noted)

On-Resistance vs. Junction Temperature

On-Resistance vs. Gate-to-Source Voltage

Source Drain Diode Forward Voltage

Threshold Voltage

Drain Source Breakdown vs. Junction Temperature

Safe Operating Area
Note

- $V_{GS} >$ minimum V_{GS} at which $R_{DS(on)}$ is specified

**THERMAL RATINGS** ($T_A = 25\text{ }^{\circ}\text{C}$, unless otherwise noted)**Normalized Thermal Transient Impedance, Junction-to-Ambient****Normalized Thermal Transient Impedance, Junction-to-Foot****Note**

- The characteristics shown in the two graphs
 - Normalized Transient Thermal Impedance Junction-to-Ambient ($25\text{ }^{\circ}\text{C}$)
 - Normalized Transient Thermal Impedance Junction-to-Foot ($25\text{ }^{\circ}\text{C}$)
 are given for general guidelines only to enable the user to get a “ball park” indication of part capabilities. The data are extracted from single pulse transient thermal impedance characteristics which are developed from empirical measurements. The latter is valid for the part mounted on printed circuit board - FR4, size 1" x 1" x 0.062", double sided with 2 oz. copper, 100 % on both sides. The part capabilities can widely vary depending on actual application parameters and operating conditions.

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SOIC (NARROW): 8-LEAD

JEDEC Part Number: MS-012



DIM	MILLIMETERS		INCHES	
	Min	Max	Min	Max
A	1.35	1.75	0.053	0.069
A ₁	0.10	0.20	0.004	0.008
B	0.35	0.51	0.014	0.020
C	0.19	0.25	0.0075	0.010
D	4.80	5.00	0.189	0.196
E	3.80	4.00	0.150	0.157
e	1.27 BSC		0.050 BSC	
H	5.80	6.20	0.228	0.244
h	0.25	0.50	0.010	0.020
L	0.50	0.93	0.020	0.037
q	0°	8°	0°	8°
S	0.44	0.64	0.018	0.026
ECN: C-06527-Rev. I, 11-Sep-06				
DWG: 5498				

RECOMMENDED MINIMUM PADS FOR SO-8



Recommended Minimum Pads
Dimensions in Inches/(mm)

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